

General Description

The MDS1754 uses advanced MagnaChip's Trench MOSFET Technology to provide high performance in on-state resistance, switching performance and reliability.

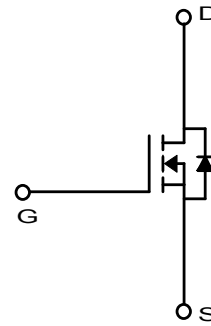
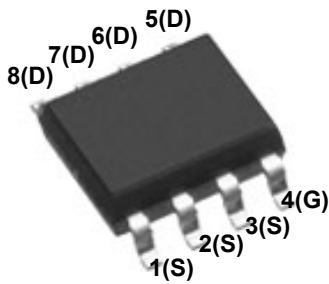
Low $R_{DS(ON)}$, Low Gate Charge can be offering superior benefit in the application.

Features

- $V_{DS} = 40V$
- $I_D = 7.6 (V_{GS} = 10V)$
- $R_{DS(ON)}$
 $< 29m\Omega @ V_{GS} = 10V$
 $< 37m\Omega @ V_{GS} = 4.5V$

Applications

- Inverters
- General purpose applications



Absolute Maximum Ratings ($T_A = 25^\circ$ unless otherwise noted)

Characteristics	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	40	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current (Note 1)	I_D	7.6	A
Pulsed Drain Current	I_{DM}	50	A
Power Dissipation	P_D	2.5	W
Single Pulse Avalanche Energy (Note 2)	E_{AS}	18	mJ
Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ C$

Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	50	$^\circ C/W$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	25	

Ordering Information

Part Number	Temp. Range	Package	Packing	RoHS Status
MDS1754RH	-55~150°C	SOIC-8	Tape & Reel	Halogen Free

Electrical Characteristics (T_J =25°C unless otherwise noted)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V	40	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.0	1.8	3.0	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 32V, V _{GS} = 0V	-	-	1	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	-	-	±0.1	
Drain-Source ON Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 7.6A	-	22	29	mΩ
		V _{GS} = 4.5V, I _D = 6.8A	-	28	37	
Forward Transconductance	g _{FS}	V _{DS} = 10V, I _D = 7.6A	-	20	-	S
Dynamic Characteristics						
Total Gate Charge	Q _g	V _{DD} = 28V, I _D = 7.6A, V _{GS} = 10V	-	9.2	-	nC
Gate-Source Charge	Q _{gs}		-	1.7	-	
Gate-Drain Charge	Q _{gd}		-	2.2	-	
Input Capacitance	C _{iss}	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	-	440	-	pF
Reverse Transfer Capacitance	C _{riss}		-	38	-	
Output Capacitance	C _{oss}		-	76	-	
Turn-On Delay Time	t _{d(on)}	V _{GS} = 10V, V _{DD} = 20V, I _D = 1A, R _{GEN} =3.3Ω	-	5.9	-	ns
Turn-On Rise Time	t _r		-	17.3	-	
Turn-Off Delay Time	t _{d(off)}		-	16.5	-	
Turn-Off Fall Time	t _f		-	10.7	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V _{SD}	I _S = 7.6A, V _{GS} = 0V	-	0.88	1.2	V
Reverse Recovery Time	t _{rr}	I _S = 7.6A, di/dt=100A/us	-	35	-	ns
Reverse Recovery Charge	Q _{rr}		-	8.8	-	nC

Notes :

1. Surface mounted RF4 board with 2oz. Copper.
2. Starting T_J=25°C, L=1mH, I_{AS}=6A V_{DD}=20V, V_{GS}=10V

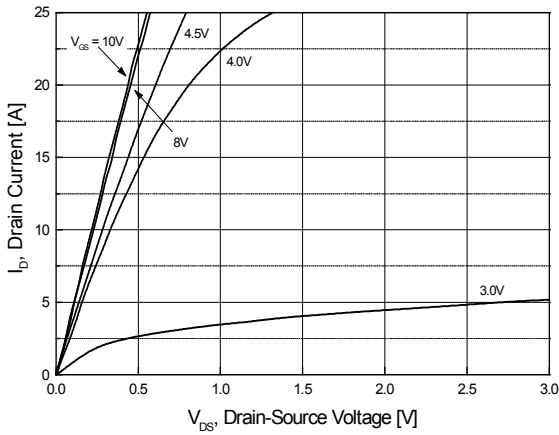


Fig.1 On-Region Characteristics

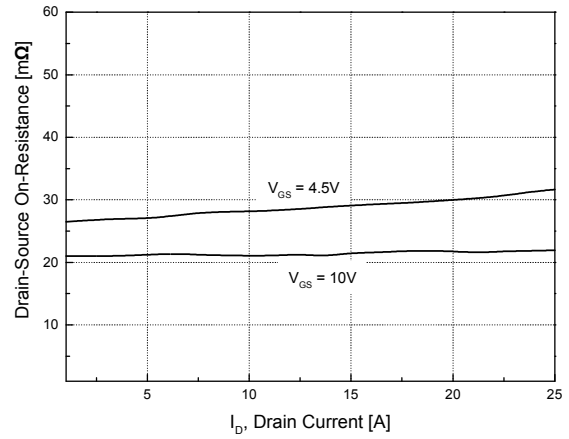


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

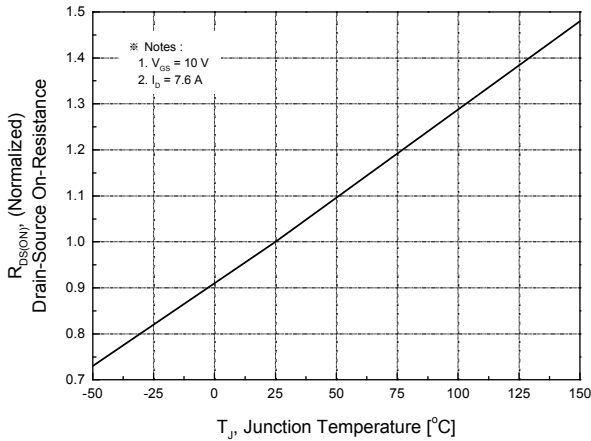


Fig.3 On-Resistance Variation with Junction Temperature

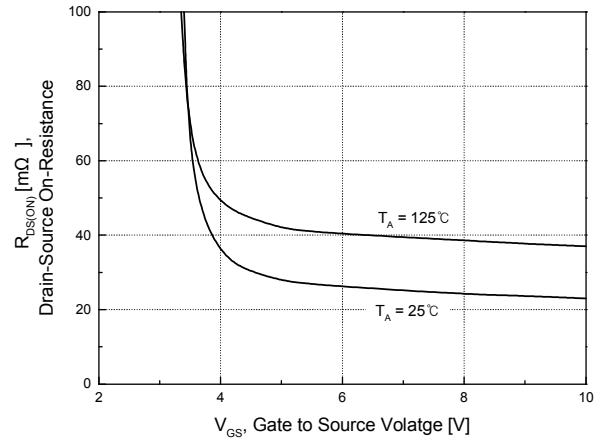


Fig.4 On-Resistance Variation with Gate to Source Voltage

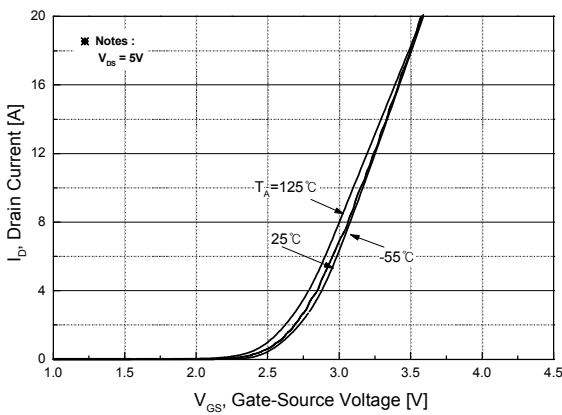


Fig.5 Transfer Characteristics

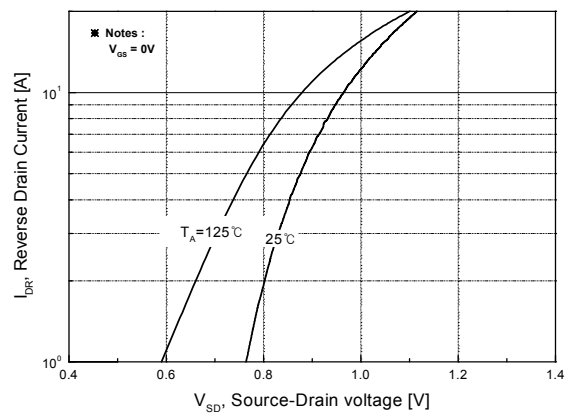


Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature

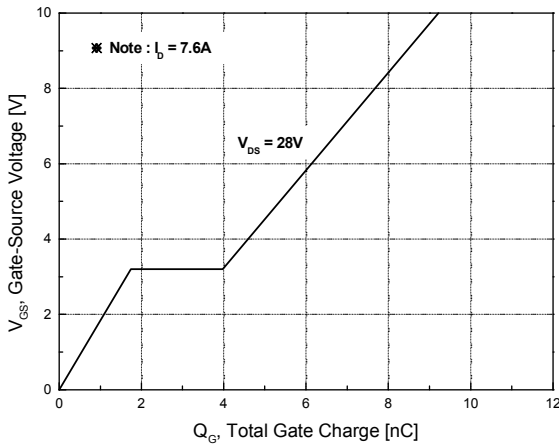


Fig.7 Gate Charge Characteristics

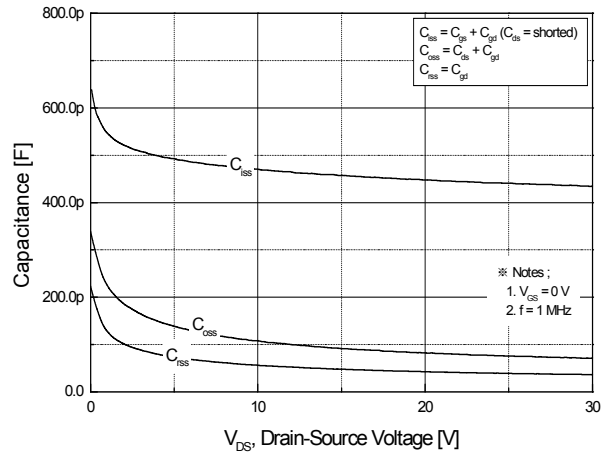


Fig.8 Capacitance Characteristics

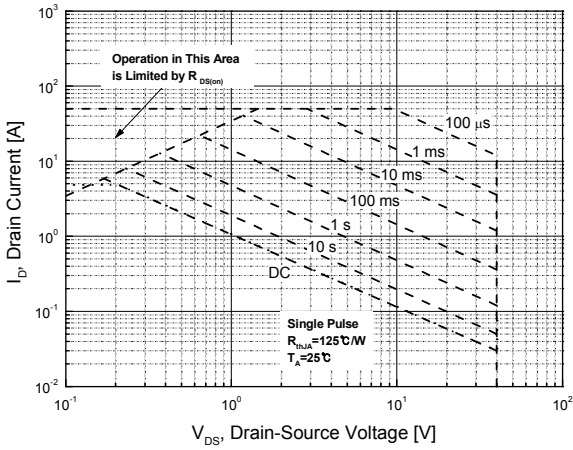


Fig.9 Maximum Safe Operating Area

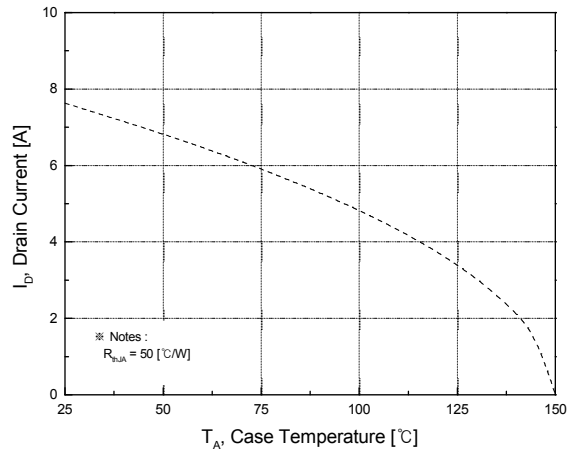


Fig.10 Maximum Drain Current vs. Case Temperature

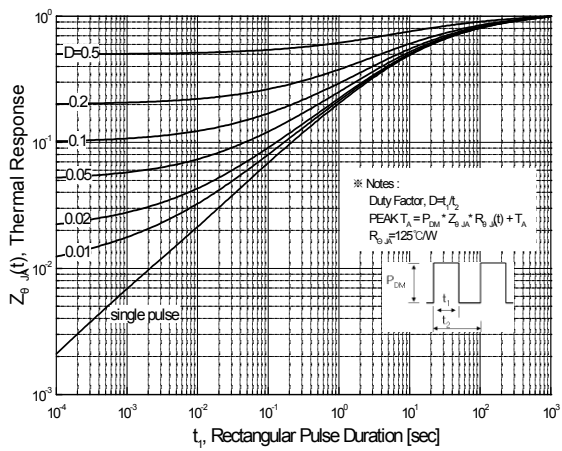
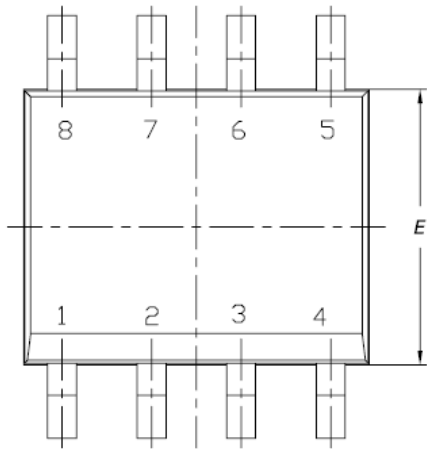


Fig.11 Transient Thermal Response Curve

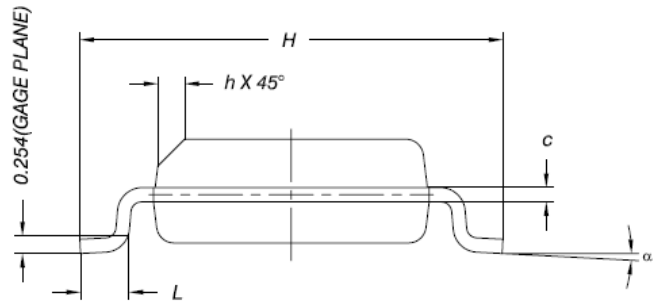
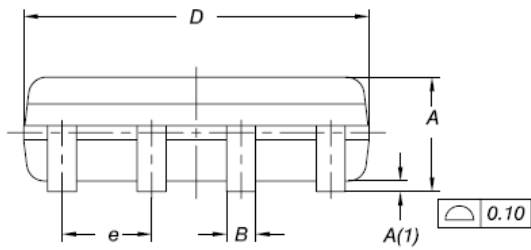
Physical Dimensions

8 Leads, SOIC

Dimensions are in millimeters unless otherwise specified



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	1.35	1.55	1.75
A(1)	0.10	0.175	0.25
B	0.38	0.445	0.51
C	0.19	0.22	0.25
D	4.80	4.90	5.00
E	3.80	3.90	4.00
e	1.27 BSC		
H	5.80	6.00	6.20
L	0.50	0.715	0.93
α	0°	4°	8°
h	0.25	0.375	0.50



Worldwide Sales Support Locations

U.S.A

Sunnyvale Office

787 N. Mary Ave. Sunnyvale
CA 94085 U.S.A
Tel : 1-408-636-5200
Fax : 1-408-213-2450
E-Mail : americasales@magnachip.com

Chicago Office

2300 Barrington Road, Suite 330
Hoffman Estates, IL 60195 U.S.A
Tel : 1-847-882-0951
Fax : 1-847-882-0998

U.K

Knyvett House The Causeway,
Staines Middx, TW18 3BA, U.K.
Tel : +44 (0) 1784-898-8000
Fax : +44 (0) 1784-895-115
E-Mail : europesales@magnachip.com

Japan

Tokyo Office

Shinbashi 2-chome MT bldg
4F 2-5-5 Shinbashi, Minato-ku
Tokyo, 105-0004 Japan
Tel : 81-3-3595-0632
Fax : 81-3-3595-0671
E-Mail : japansales@magnachip.com

Osaka Office

3F, Shin-Osaka MT-2 Bldg
3-5-36 Miyahara Yodogawa-Ku
Osaka, 532-0003 Japan
Tel : 81-6-6394-8224
Fax : 81-6-6394-8282
E-Mail : osakasales@magnachip.com

Taiwan R.O.C

2F, No.61, Chowize Street, Nei Hu
Taipei, 114 Taiwan R.O.C
Tel : 886-2-2657-7898
Fax : 886-2-2657-8751
E-Mail : taiwansales@magnachip.com

China

Hong Kong Office

Office 03, 42/F, Office Tower Convention Plaza
1 Harbour Road, Wanchai, Hong Kong
Tel : 852-2828-9700
Fax : 852-2802-8183
E-Mail : chinasales@magnachip.com

Shenzhen Office

Room 1803, 18/F
International Chamber of Commerce Tower
Fuhua 3 Road, Futian District
ShenZhen, China
Tel : 86-755-8831-5561
Fax : 86

Shangh

Ste 190:
Shanghai, China
Tel : 86-21-6373-5181
Fax : 86-21-6373-6640

Korea

891, Daechi-Dong, Kangnam-Gu
Seoul, 135-738 Korea
Tel : 82-2-6903-3451
Fax : 82-2-6903-3668 ~9
Email : koreasales@magnachip.com

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